

N-channel TrenchMOS standard level FET

Rev. 2 — 2 February 2011

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

	Guick reference ua	ta				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	63	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	200	W
Static cha	racteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	50	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	17	20	mΩ
Avalanche	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 60 \text{ A}; \text{V}_{\text{sup}} \leq 100 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 10 \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	400	mJ

Suitable for standard level gate drive sources

Suitable for thermally demanding environments due to 175 °C rating

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Motors, lamps and solenoids

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2. Pinning information

Table 2.	Pinning information			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK7620-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

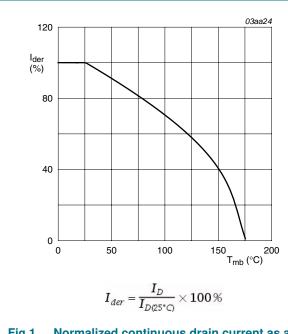
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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	63	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	44	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>	-	253	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	200	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	-	63	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	253	А
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 60 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	400	mJ





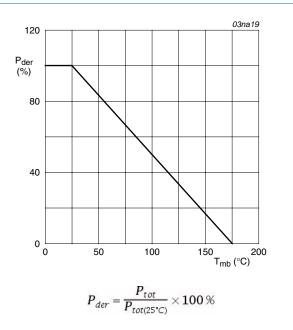
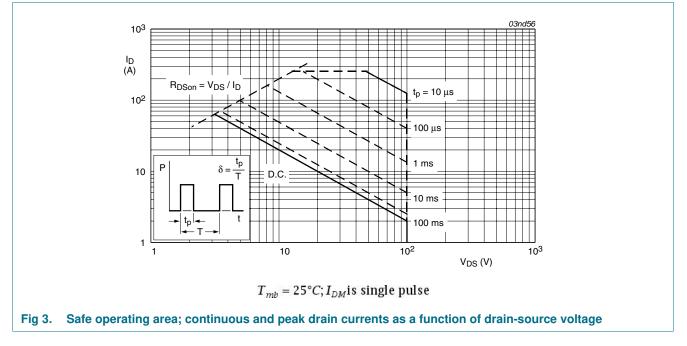


Fig 2. Normalized total power dissipation as a function of mounting base temperature

BUK7620-100A

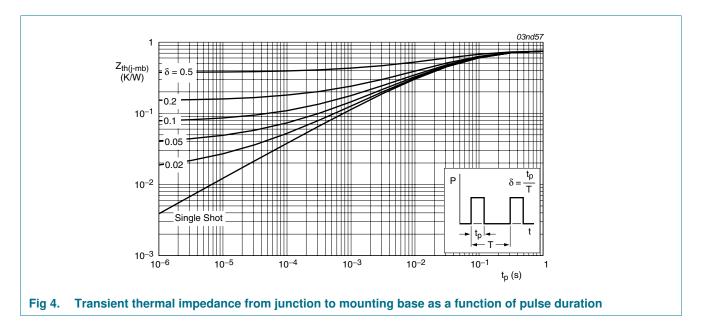
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	0.75	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W



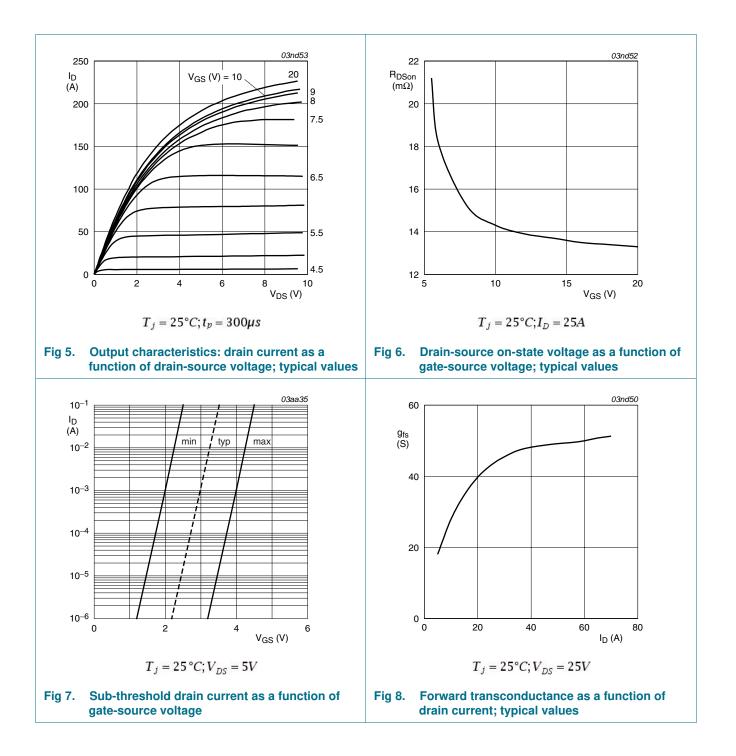
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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 11</u>	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 11</u>	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	1	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	50	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	17	20	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	3430	4373	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	440	525	pF
C _{rss}	reverse transfer capacitance		-	260	352	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_{L} = 1.2 Ω ; V_{GS} = 10 V;	-	21	-	ns
t _r	rise time	R _{G(ext)} = 10 Ω; T _j = 25 °C	-	87	-	ns
t _{d(off)}	turn-off delay time		-	108	-	ns
t _f	fall time		-	56	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; T _j = 25 °C	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; T _j = 25 °C	-	7.5	-	nH
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs;	-	76	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	282	-	nC

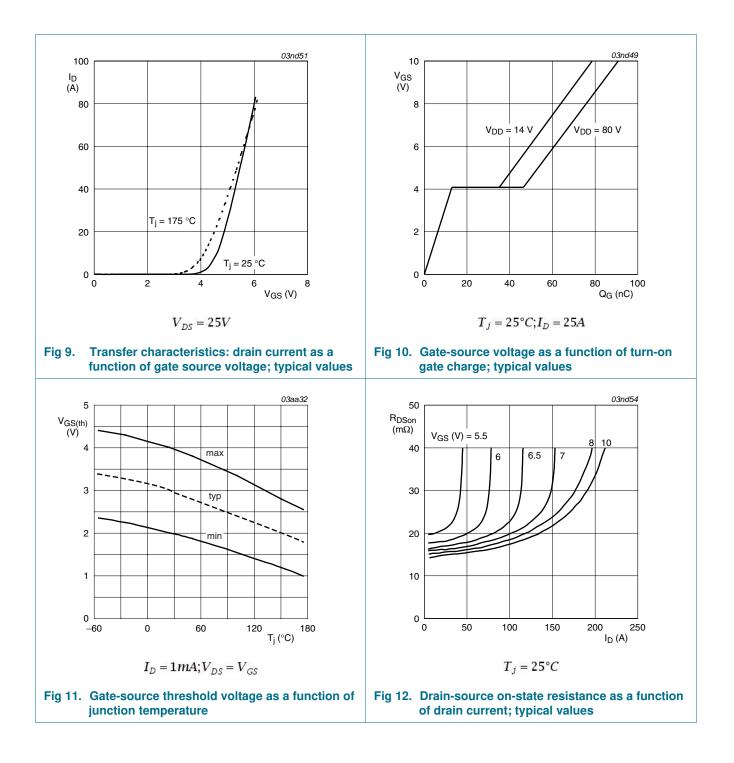
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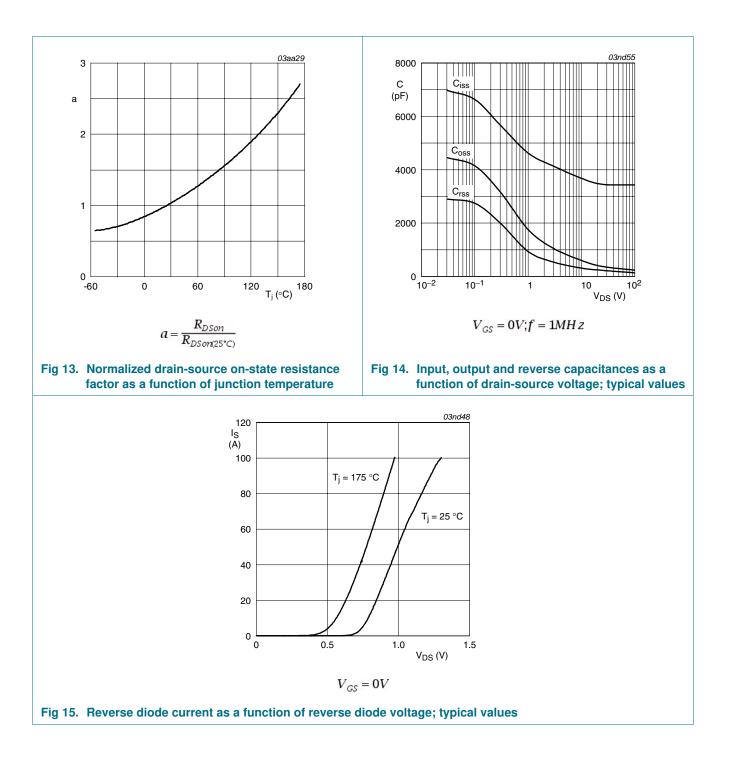
BUK7620-100A

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7. Package outline

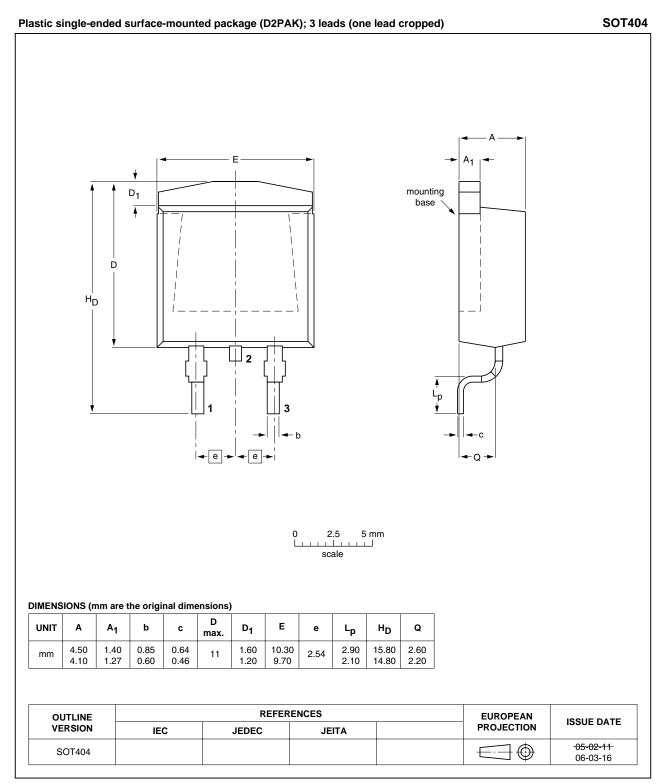


Fig 16. Package outline SOT404 (D2PAK)

BUK7620-100A Product data sheet

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8. Revision history

Table 7.	Revision history				
Documen	t ID	Release date	Data sheet status	Change notice	Supersedes
BUK7620-	100A v.2	20110202	Product data sheet	-	BUK7520_7620_100A-01
Modifications:		guidelines c	of NXP Semiconductors.	5	omply with the new identity
		0	have been adapted to the	1 3	
		 Type number 	er BUK7620-100A separa	ated from data she	et BUK7520_7620_100A-01.
BUK7520	_7620_100A-01	20010205	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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